Abstracts

A general noise and S-parameter deembedding procedure for on-wafer high-frequency noise measurements of MOSFETs

C.-H. Chen and M.J. Deen. "A general noise and S-parameter deembedding procedure for on-wafer high-frequency noise measurements of MOSFETs." 2001 Transactions on Microwave Theory and Techniques 49.5 (May 2001 [T-MTT]): 1004-1005.

A general deembedding procedure using one "OPEN" and two "THRU" dummy structures for noise and scattering parameter deembedding based on cascade configurations is presented in this paper. This technique does not require any equivalent-circuit modeling of probe pads or interconnections. This deembedding procedure is valid for designs having interconnections with any kinds of geometries and for devices operated at frequencies of several tens of gigahertz.

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